Amendments to the Specification:

Amend the paragraph beginning on page 8, line 7 as follows:

Continuing with FIG. 4, a cross sectional view illustrating spacer formation and source/drain implant of the semiconductor device 300 in accordance with an aspect of the present invention is depicted. Sidewall spacers 412, 413, and 414 are formed and located, adjacent to the gate oxide layer ~~404~~ 304 and the polysilicon gate ~~406~~ 306. Subsequently, a source/drain implant is performed with a n-type dopant such as As and/or P, which forms deep source/drain regions ~~407,~~ 408.